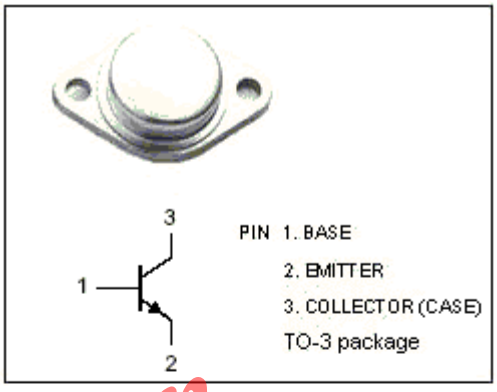
isc Silicon NPN Power Transistor 2SD582

DESCRIPTION

- Collector-Emitter Breakdown Voltage-
  : $V_{(BR)CEO}$= 140V(Min.)
- Collector-Emitter Saturation Voltage-
  : $V_{CE(sat)}$= 1.5V(Max.)@ I_C= 7A
- Complement to Type 2SB612

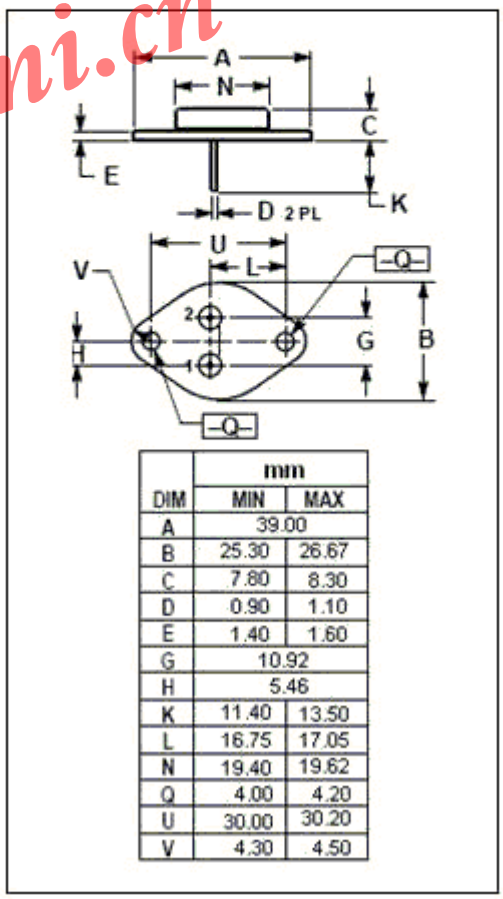


APPLICATIONS

- Designed for 80~100W audio amplifier power output applications.

ABSOLUTE MAXIMUM RATINGS(T_a=25℃)

SYMBOL	PARAMETER	MAX	UNIT
V_{CBO}	Collector-Base Voltage	180	V
V_{CEO}	Collector-Emitter Voltage	140	V
V_{EBO}	Emitter-Base Voltage	6	V
I_C	Collector Current-Continuous	12	A
I_{CM}	Collector Current-Peak	15	A
I_B	Base Current-Continuous	2	A
P_C	Collector Power Dissipation @T_C=25℃	100	W
T_j	Junction Temperature	150	℃
T_{stg}	Storage Temperature Range	-55~150	℃



DIM	mm MIN	MAX
A	39.00	
B	25.30	26.67
C	7.80	8.30
D	0.90	1.10
E	1.40	1.60
G	10.92	
H	5.46	
K	11.40	13.50
L	16.75	17.05
N	19.40	19.62
Q	4.00	4.20
U	30.00	30.20
V	4.30	4.50

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ELECTRICAL CHARACTERISTICS

T_C=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)CEO}$	Collector-Emitter Breakdown Voltage	I_C= 50mA; R_{BE}= ∞	140			V
$V_{(BR)EBO}$	Emitter-Base Breakdown Voltage	I_E= 5mA; I_C= 0	6			V
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	I_C= 7A; I_B= 0.7A			1.5	V
$V_{BE(on)}$	Base-Emitter On Voltage	I_C= 1A; V_{CE}= 5V			1.5	V
I_{CBO}	Collector Cutoff Current	V_{CB}= 160V; I_E= 0			10	μA
h_{FE-1}	DC Current Gain	I_C= 1A; V_{CE}= 5V	35		200	
h_{FE-2}	DC Current Gain	I_C= 7A; V_{CE}= 5V	20			

◆ **h_{FE-1} Classifications**

A	B	C
35-70	60-120	100-200